

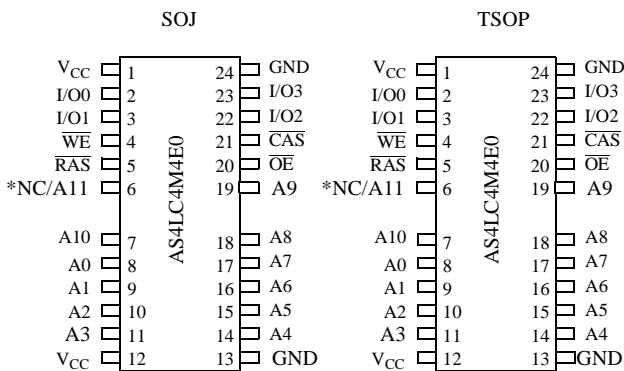


4Mx4 CMOS DRAM (EDO) Family

Features

- Organization: 4,194,304 words × 4 bits
- High speed
 - 50/60 ns $\overline{\text{RAS}}$ access time
 - 25/30 ns column address access time
 - 12/15 ns $\overline{\text{CAS}}$ access time
- Low power consumption
 - Active: 500 mW max
 - Standby: 3.6 mW max, CMOS I/O
- Extended data out
- Refresh
 - 4096 refresh cycles, 64 ms refresh interval for AS4LC4M4E0
 - 2048 refresh cycles, 32 ms refresh interval for AS4LC4M4E1
 - $\overline{\text{RAS}}$ -only or $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh or self-refresh
- TTL-compatible, three-state I/O
- JEDEC standard package
 - 300 mil, 24/26-pin SOJ
- 3V power supply
- Industrial and commercial temperature available

Pin arrangement



* NC on 2K refresh version; A11 on 4K refresh version

Pin designation

Pin(s)	Description
A0 to A11	Address inputs
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Write enable
I/O0 to I/O3	Input/output
$\overline{\text{OE}}$	Output enable
V_{CC}	Power
GND	Ground

Selection guide

	Symbol	AS4LC4M4E0/E1-50	AS4LC4M4E0/E1-60	Unit
Maximum $\overline{\text{RAS}}$ access time	t_{RAC}	50	60	ns
Maximum column address access time	t_{CAA}	25	30	ns
Maximum $\overline{\text{CAS}}$ access time	t_{CAC}	12	15	ns
Maximum output enable ($\overline{\text{OE}}$) access time	t_{OEA}	13	15	ns
Minimum read or write cycle time	t_{RC}	80	100	ns
Minimum fast page mode cycle time	t_{PC}	25	30	ns
Maximum operating current	I_{CC1}	120	110	mA
Maximum CMOS standby current	I_{CC5}	1.0	1.0	mA



Functional description

The AS4LC4M4E0 and AS4LC4M4E1 are high performance 16-megabit CMOS Dynamic Random Access Memories (DRAM) organized as 4,194,304 words \times 4 bits. The devices are fabricated using advanced CMOS technology and innovative design techniques resulting in high speed, extremely low power and wide operating margins at component and system levels. The Alliance 16Mb DRAM family is optimized for use as main memory in PC, workstation, router and switch applications.

These products feature a high speed page mode operation where read and write operations within a single row (or page) can be executed at very high speed by toggling column addresses within that row. Row and column addresses are alternately latched into input buffers using the falling edge of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ inputs respectively. Also, $\overline{\text{RAS}}$ is used to make the column address latch transparent, enabling application of column addresses prior to $\overline{\text{CAS}}$ assertion.

Extended data out (EDO) read mode enables 60MHz operation using 60ns devices. In contrast to 'fast page mode' devices, data remains active on outputs after $\overline{\text{CAS}}$ is de-asserted high, giving system logic more time to latch the data. Use $\overline{\text{OE}}$ and $\overline{\text{WE}}$ to control output impedance and prevent bus contention during read-modify-write and shared bus applications. Outputs also go to high impedance at the last occurrence of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ going high.

Refresh on the 4096 address combinations of A0 to A11 must be performed every 64 ms using:

- $\overline{\text{RAS}}$ -only refresh: $\overline{\text{RAS}}$ is asserted while $\overline{\text{CAS}}$ is held high. Each of the 4096 rows must be strobed. Outputs remain high impedance.
- Hidden refresh: $\overline{\text{CAS}}$ is held low while $\overline{\text{RAS}}$ is toggled. Refresh address is generated internally. Outputs remain low impedance with previous valid data.
- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh (CBR): $\overline{\text{CAS}}$ is asserted prior to $\overline{\text{RAS}}$. Refresh address is generated internally. Outputs are high-impedance ($\overline{\text{OE}}$ and $\overline{\text{WE}}$ are don't care).
- Normal read or write cycles refresh the row being accessed.
- Self-refresh cycles

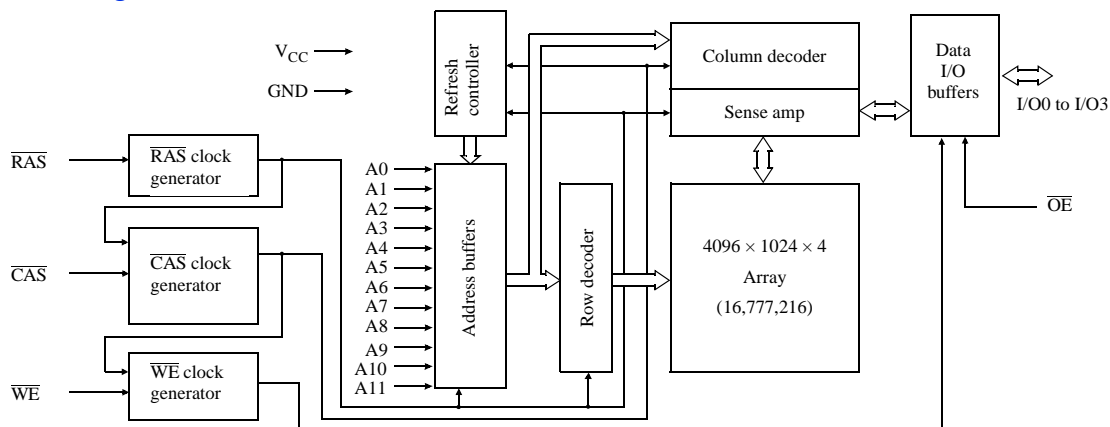
Refresh on the 2048 address combinations of A0 to A10 must be performed every 32 ms using:

- $\overline{\text{RAS}}$ -only refresh: $\overline{\text{RAS}}$ is asserted while $\overline{\text{CAS}}$ is held high. Each of the 2048 rows must be strobed. Outputs remain high impedance.
- Hidden refresh: $\overline{\text{CAS}}$ is held low while $\overline{\text{RAS}}$ is toggled. Refresh address is generated internally. Outputs remain low impedance with previous valid data.
- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh (CBR): $\overline{\text{CAS}}$ is asserted prior to $\overline{\text{RAS}}$. Refresh address is generated internally. Outputs are high-impedance ($\overline{\text{OE}}$ and $\overline{\text{WE}}$ are don't care).
- Normal read or write cycles refresh the row being accessed.
- Self-refresh cycles

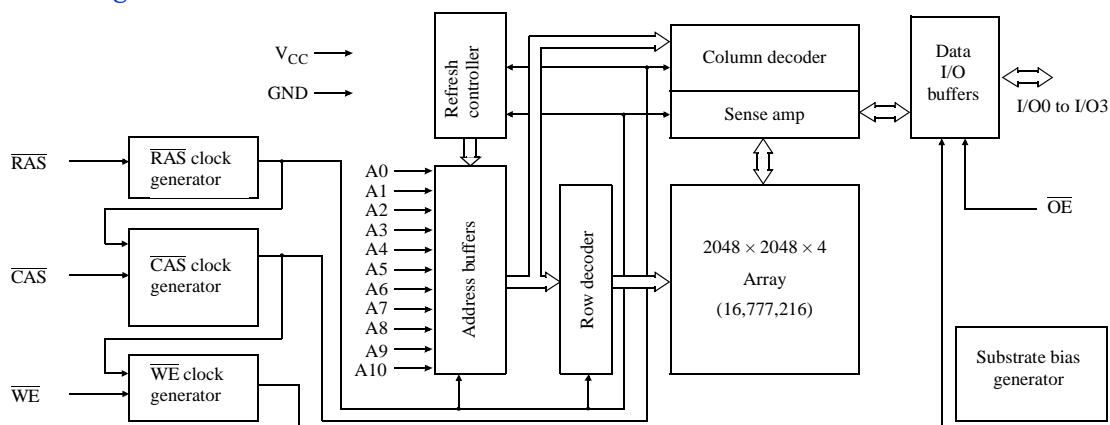
The AS4LC4M4E0 and AS4LC4M4E1 are available in the standard 24/26-pin plastic SOJ and 24/26-pin plastic TSOP packages. The AS4LC4M4E0 and AS4LC4M4E1 operate with a single power supply of $3\text{V} \pm 0.3\text{V}$. All provide TTL compatible inputs and outputs.



Logic block diagram for 4K refresh



Logic block diagram for 2K refresh



Recommended operating conditions

Parameter		Symbol	Min	Nominal	Max	Unit
Supply voltage		V_{CC}	3.0	3.3	3.6	V
		GND	0.0	0.0	0.0	V
Input voltage		V_{IH}	2.0	–	$V_{CC}+0.5V$	V
		V_{IL}	-0.5^{\dagger}	–	0.8	V
Ambient operating temperature	Commercial	T_A	0	–	70	°C
	Industrial		-40	–	85	

[†] V_{IL} min -3.0V for pulse widths less than 5 ns. Recommended operating conditions apply throughout this document unless otherwise specified.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Input voltage	V_{in}	-1.0	4.6	V
Input voltage (DQs)	V_{DQ}	-1.0	4.6	V
Power supply voltage	V_{CC}	-1.0	4.6	V
Storage temperature (plastic)	T_{STG}	-55	+150	°C
Soldering temperature × time	T_{SOLDER}	–	260×10	°C × sec



Parameter	Symbol	Min	Max	Unit
Power dissipation	P_D	–	0.5	W
Short circuit output current	I_{out}	–	50	mA

DC electrical characteristics

Parameter	Symbol	Test conditions	-50		-60		Unit	Notes
			Min	Max	Min	Max		
Input leakage current	I_{IL}	$0V \leq V_{in} \leq +V_{CC}$ (max) Pins not under test = 0V	-5	+5	-5	+5	μA	
Output leakage current	I_{OL}	D_{OUT} disabled, $0V \leq V_{out} \leq +V_{CC}$ (max)	-5	+5	-5	+5	μA	
Operating power supply current	I_{CC1}	\overline{CAS} , Address cycling; $t_{RC} = \min$	–	120	–	110	mA	1,2
TTL standby power supply current	I_{CC2}	$\overline{RAS} = \overline{CAS} \geq V_{IH}$	–	2.0	–	2.0	mA	
Average power supply current, \overline{RAS} refresh mode or CBR	I_{CC3}	\overline{RAS} cycling, $\overline{CAS} \geq V_{IH}$, $t_{RC} = \min$ of \overline{RAS} low after \overline{CAS} low.	–	120	–	110	mA	1
EDO page mode average power supply current	I_{CC4}	$\overline{RAS} = V_{IL}$, \overline{CAS} , address cycling; $t_{HPC} = \min$	–	90	–	80	mA	1, 2
CMOS standby power supply current	I_{CC5}	$\overline{RAS} = \overline{CAS} = V_{CC} - 0.2V$	–	1.0	–	1.0	mA	
Output voltage	V_{OH}	$I_{OUT} = -2.0$ mA	2.4	–	2.4	–	V	
	V_{OL}	$I_{OUT} = 2.0$ mA	–	0.4	–	0.4	V	
\overline{CAS} before \overline{RAS} refresh current	I_{CC6}	\overline{RAS} , \overline{CAS} cycling, $t_{RC} = \min$	–	120	–	110	mA	
Self refresh current	I_{CC7}	$\overline{RAS} = \overline{CAS} \leq 0.2V$, $\overline{WE} = \overline{OE} \geq V_{CC} - 0.2V$, all other inputs at 0.2V or $V_{CC} - 0.2V$	–	0.6	–	0.6	mA	



AC parameters common to all waveforms

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RC}	Random read or write cycle time	80	–	100	–	ns	
t_{RP}	\overline{RAS} precharge time	30	–	40	–	ns	
t_{RAS}	\overline{RAS} pulse width	50	10K	60	10K	ns	
t_{CAS}	\overline{CAS} pulse width	8	10K	10	10K	ns	
t_{RCD}	\overline{RAS} to \overline{CAS} delay time	15	35	15	43	ns	6
t_{RAD}	\overline{RAS} to column address delay time	12	25	12	30	ns	7
t_{RSH}	\overline{CAS} to \overline{RAS} hold time	10	–	10	–	ns	
t_{CSH}	\overline{RAS} to \overline{CAS} hold time	40	–	50	–	ns	
t_{CRP}	\overline{CAS} to \overline{RAS} precharge time	5	–	5	–	ns	
t_{ASR}	Row address setup time	0	–	0	–	ns	
t_{RAH}	Row address hold time	8	–	10	–	ns	
t_T	Transition time (rise and fall)	1	50	1	50	ns	4,5
t_{REF}	Refresh period	–	64	–	64	ms	3
t_{CP}	\overline{CAS} precharge time	8	–	10	–	ns	
t_{RAL}	Column address to \overline{RAS} lead time	25	–	30	–	ns	
t_{ASC}	Column address setup time	0	–	0	–	ns	
t_{CAH}	Column address hold time	8	–	10	–	ns	

Read cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RAC}	Access time from \overline{RAS}	–	50	–	60	ns	6
t_{CAC}	Access time from \overline{CAS}	–	12	–	15	ns	6,13
t_{AA}	Access time from address	–	25	–	30	ns	7,13
t_{RCS}	Read command setup time	0	–	0	–	ns	
t_{RCH}	Read command hold time to \overline{CAS}	0	–	0	–	ns	9
t_{RRH}	Read command hold time to \overline{RAS}	0	–	0	–	ns	9



Write cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{WCS}	Write command setup time	0	–	0	–	ns	11
t_{WCH}	Write command hold time	10	–	10	–	ns	11
t_{WP}	Write command pulse width	10	–	10	–	ns	
t_{RWL}	Write command to \overline{RAS} lead time	10	–	10	–	ns	
t_{CWL}	Write command to \overline{CAS} lead time	8	–	10	–	ns	
t_{DS}	Data-in setup time	0	–	0	–	ns	12
t_{DH}	Data-in hold time	8	–	10	–	ns	12

Read-modify-write cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RWC}	Read-write cycle time	113	–	135	–	ns	
t_{RWD}	\overline{RAS} to \overline{WE} delay time	67	–	77	–	ns	11
t_{CWD}	\overline{CAS} to \overline{WE} delay time	32	–	35	–	ns	11
t_{AWD}	Column address to \overline{WE} delay time	42	–	47	–	ns	11

Refresh cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{CSR}	\overline{CAS} setup time (\overline{CAS} -before- \overline{RAS})	5	–	5	–	ns	3
t_{CHR}	\overline{CAS} hold time (\overline{CAS} -before- \overline{RAS})	8	–	10	–	ns	3
t_{RPC}	\overline{RAS} precharge to \overline{CAS} hold time	0	–	0	–	ns	
t_{CPT}	\overline{CAS} precharge time (CBR counter test)	10	–	10	–	ns	



Hyper page mode cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{CPWD}	\overline{CAS} precharge to \overline{WE} delay time	45	–	52	–	ns	
t_{CPA}	Access time from \overline{CAS} precharge	–	28	–	35	ns	13
t_{RASP}	\overline{RAS} pulse width	50	100K	60	100K	ns	
t_{DOH}	Previous data hold time from \overline{CAS}	5	–	5	–	ns	
t_{REZ}	Output buffer turn off delay from \overline{RAS}	0	13	0	15	ns	
t_{WEZ}	Output buffer turn off delay from \overline{WE}	0	13	0	15	ns	
t_{OEZ}	Output buffer turn off delay from \overline{OE}	0	13	0	15	ns	
t_{HPC}	Hyper page mode cycle time	20	–	25	–	ns	
t_{HPRWC}	Hyper page mode RMW cycle	47	–	56	–	ns	
t_{RHCP}	\overline{RAS} hold time from \overline{CAS}	30	–	35	–	ns	

Output enable

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{CLZ}	\overline{CAS} to output in Low Z	0	–	0	–	ns	8
t_{ROH}	\overline{RAS} hold time referenced to \overline{OE}	8	–	10	–	ns	
t_{OEA}	\overline{OE} access time	–	13	–	15	ns	
t_{OED}	\overline{OE} to data delay	13	–	15	–	ns	
t_{OEZ}	Output buffer turnoff delay from \overline{OE}	0	13	0	15	ns	8
t_{OEH}	\overline{OE} command hold time	10	–	10	–	ns	
t_{OLZ}	\overline{OE} to output in Low Z	0	–	0	–	ns	
t_{OFF}	Output buffer turn-off time	0	13	0	15	ns	8,10

Self-refresh cycle

Std Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RASS}	\overline{RAS} pulse width (CBR self refresh)	100	–	100	–	μ s	
t_{RPS}	\overline{RAS} precharge time (CBR self refresh)	90	–	105	–	ns	
t_{CHS}	\overline{CAS} hold time (CBR self refresh)	8	–	10	–	ns	



Notes

- 1 I_{CC1} , I_{CC3} , I_{CC4} , and I_{CC6} are dependent on frequency.
- 2 I_{CC1} and I_{CC4} depend on output loading. Specified values are obtained with the output open.
- 3 An initial pause of 200 μ s is required after power-up followed by any 8 \overline{RAS} cycles before proper device operation is achieved. In the case of an internal refresh counter, a minimum of 8 \overline{CAS} -before- \overline{RAS} initialization cycles instead of 8 \overline{RAS} cycles are required. 8 initialization cycles are required after extended periods of bias without clocks (greater than 8 ms).
- 4 AC Characteristics assume $t_T = 2$ ns. All AC parameters are as described in AC test conditions below
- 5 V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} .
- 6 Operation within the t_{RCD} (max) limit insures that t_{RAC} (max) can be met. t_{RCD} (max) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC} .
- 7 Operation within the t_{RAD} (max) limit insures that t_{RAC} (max) can be met. t_{RAD} (max) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA} .
- 8 Assumes three state test load (5 pF and a 380 Ω Thevenin equivalent).
- 9 Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
- 10 t_{OFF} (max) defines the time at which the output achieves the open circuit condition; it is not referenced to output voltage levels. t_{OFF} is referenced from rising edge of \overline{RAS} or \overline{CAS} , whichever occurs last.
- 11 t_{WCS} , t_{WCH} , t_{RWD} , t_{CWD} and t_{AWD} are not restrictive operating parameters. They are included in the datasheet as electrical characteristics only. If $t_{WS} \geq t_{WS}$ (min) and $t_{WH} \geq t_{WH}$ (min), the cycle is an early write cycle and data out pins will remain open circuit, high impedance, throughout the cycle. If $t_{RWD} \geq t_{RWD}$ (min), $t_{CWD} \geq t_{CWD}$ (min) and $t_{AWD} \geq t_{AWD}$ (min), the cycle is a read-write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is satisfied, the condition of the data out at access time is indeterminate.
- 12 These parameters are referenced to \overline{CAS} leading edge in early write cycles and to \overline{WE} leading edge in read-write cycles.
- 13 Access time is determined by the longest of t_{CAA} or t_{CAC} or t_{CPA}
- 14 $t_{ASC} \geq t_{CP}$ to achieve t_{PC} (min) and t_{CPA} (max) values.
- 15 These parameters are sampled and not 100% tested.

AC test conditions

- Access times are measured with output reference levels of $V_{OH} = 2.4V$ and $V_{OL} = 0.4V$,
 $V_{IH} = 2.0V$ and $V_{IL} = 0.8V$
- Input rise and fall times: 2 ns

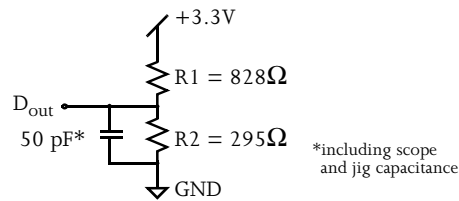


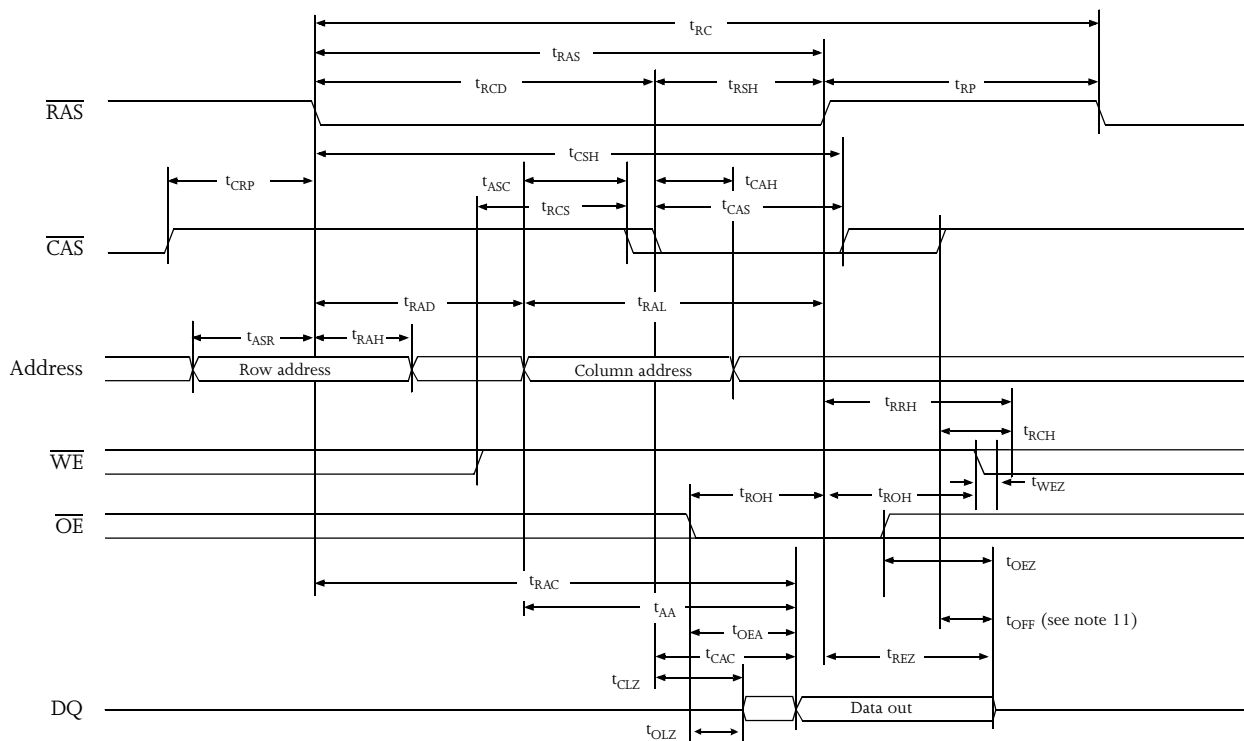
Figure B: Equivalent output load

(AS4LC4M4E0)

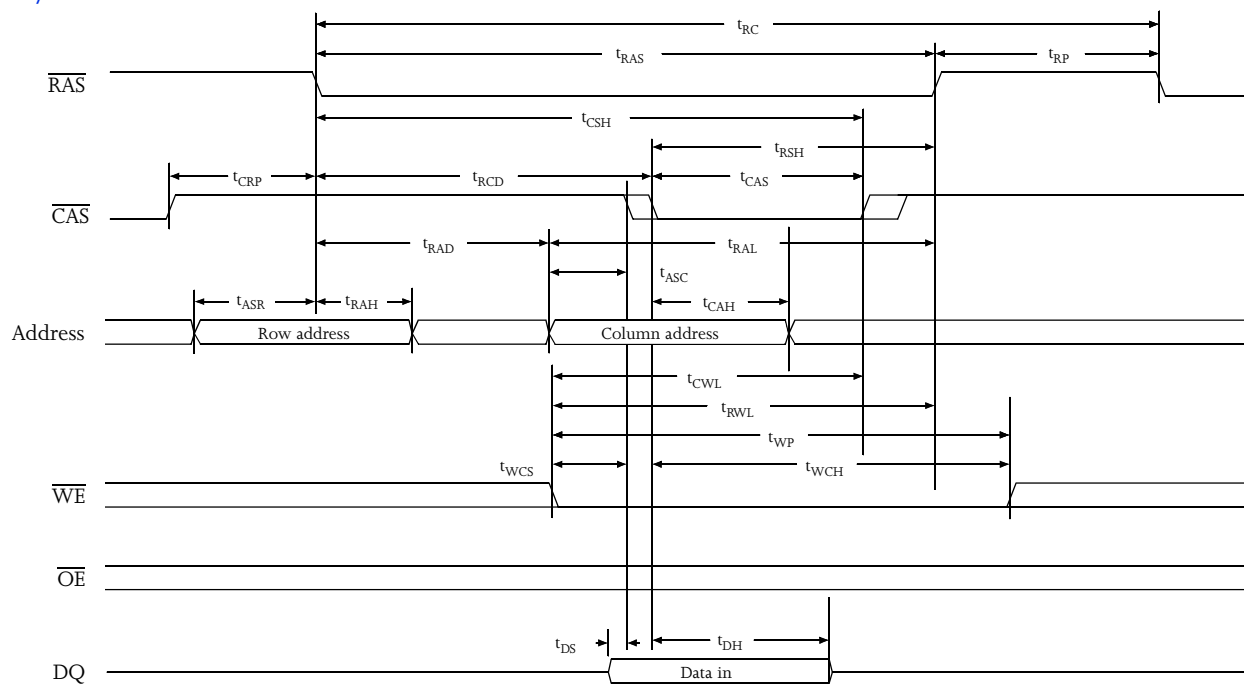
(AS4LC4M4E1)



Read waveform



Early write waveform



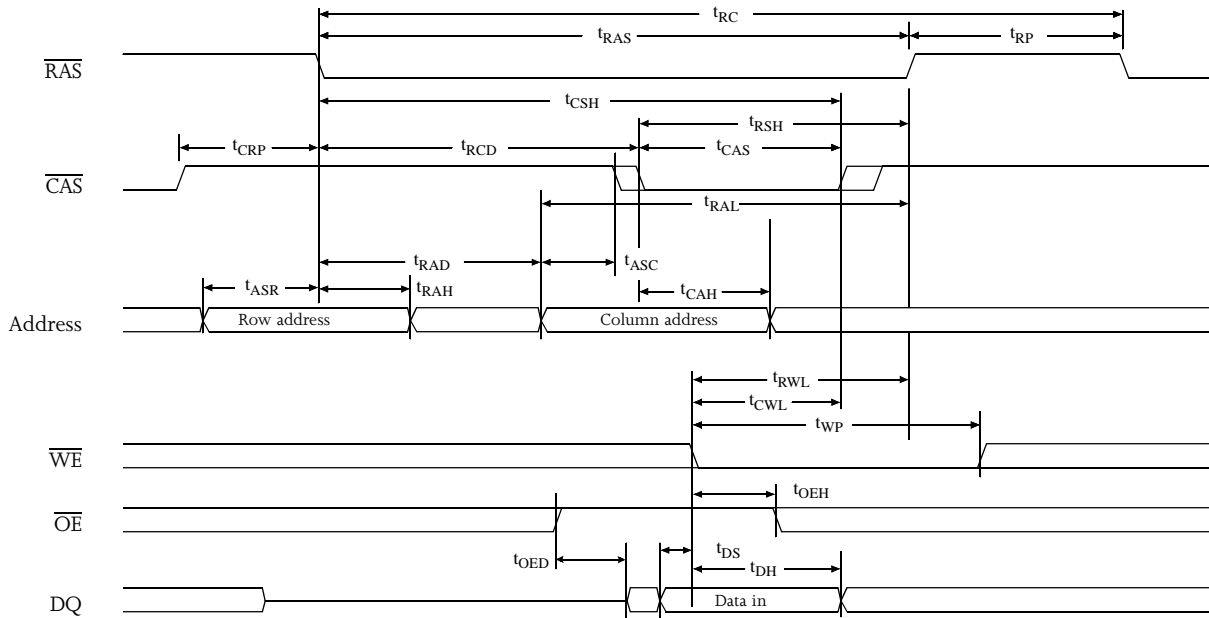
Key to switching waveform

- Rising input
- Falling input
- Undefined output/don't care

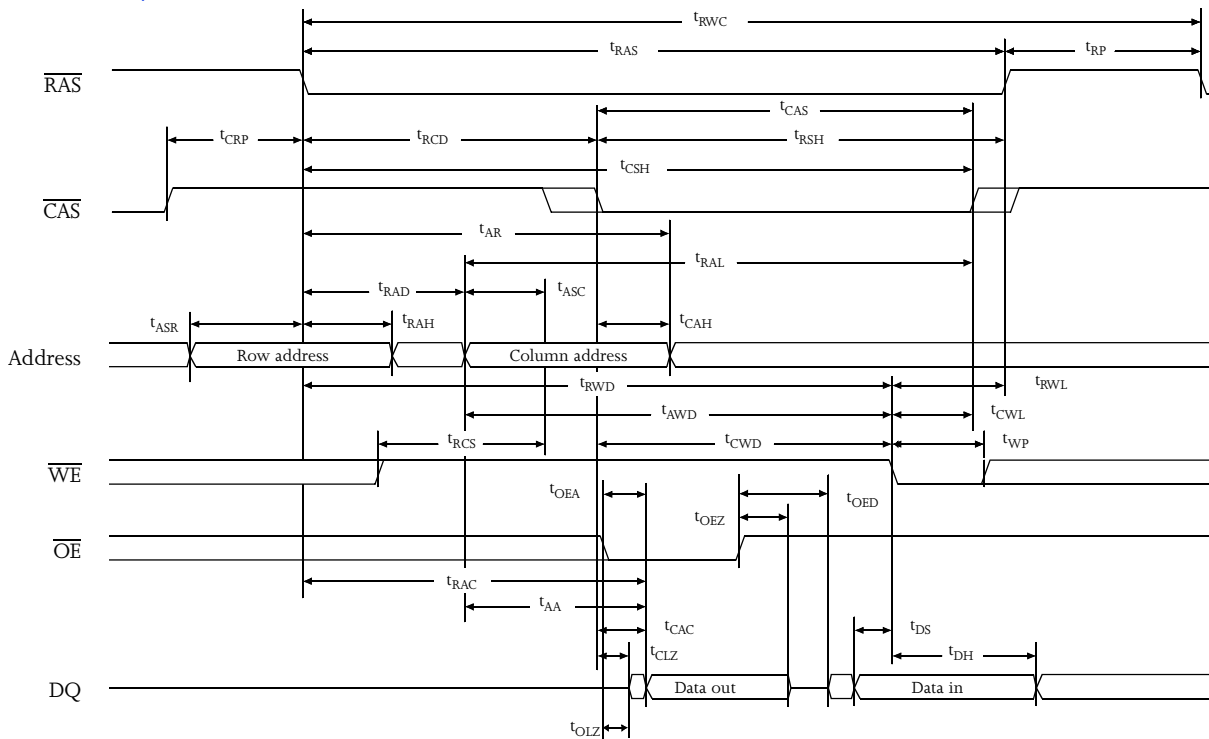


Write waveform

\overline{OE} controlled

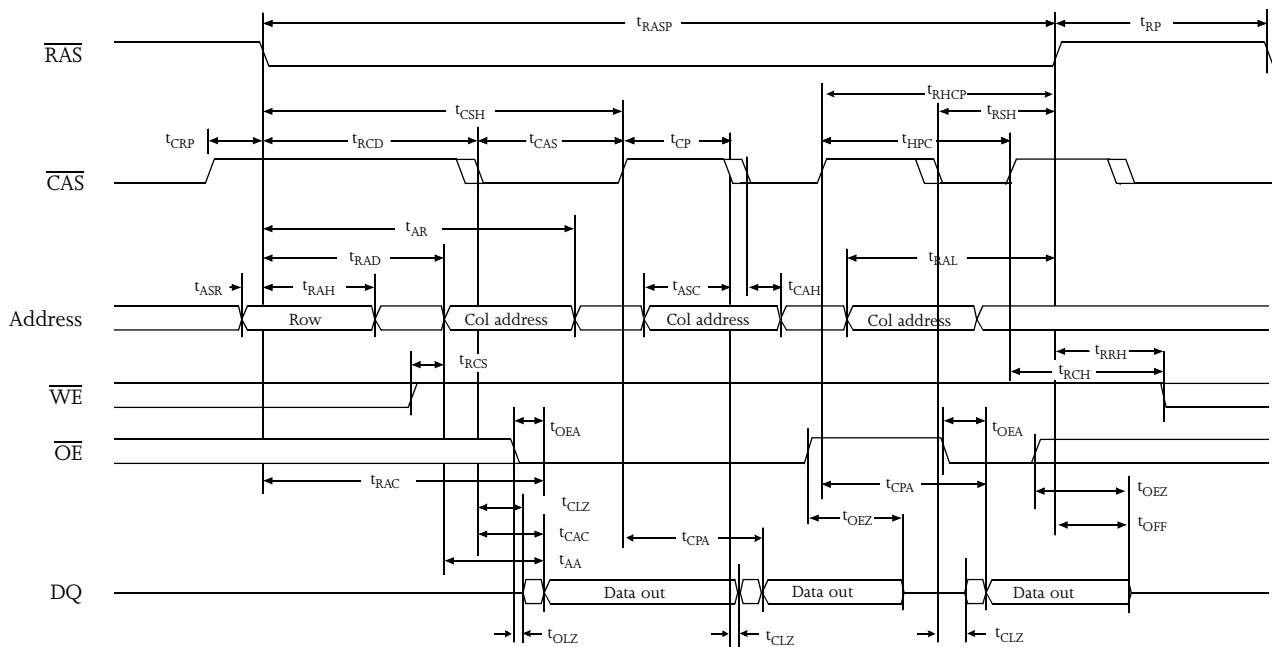


Read-modify-write waveform

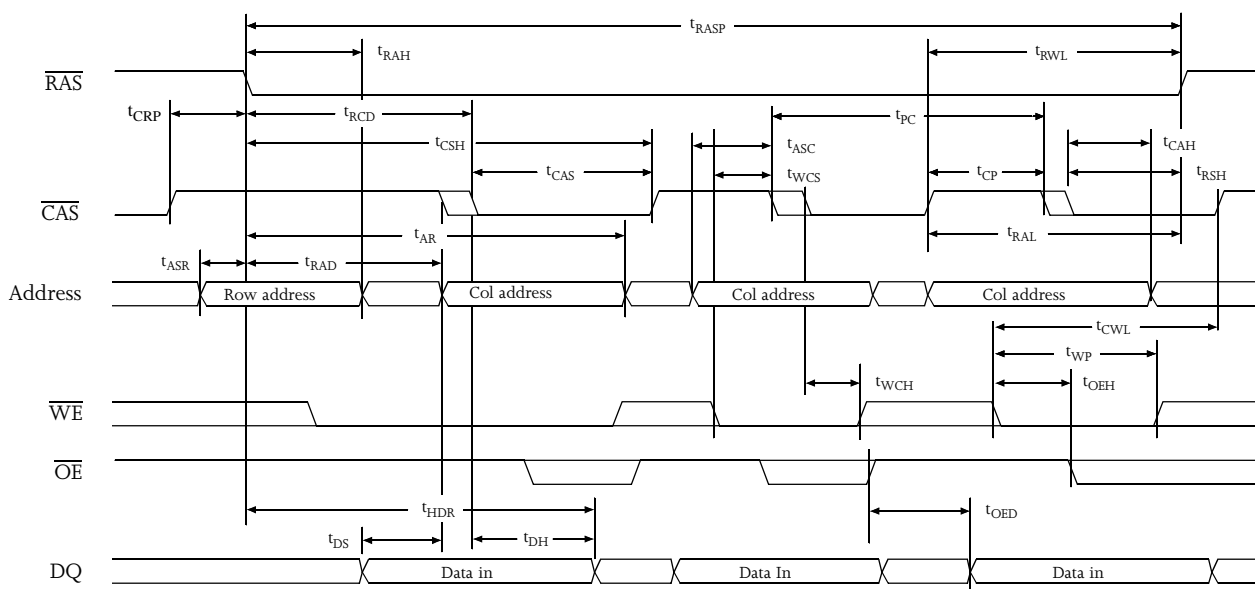




EDO page mode read waveform

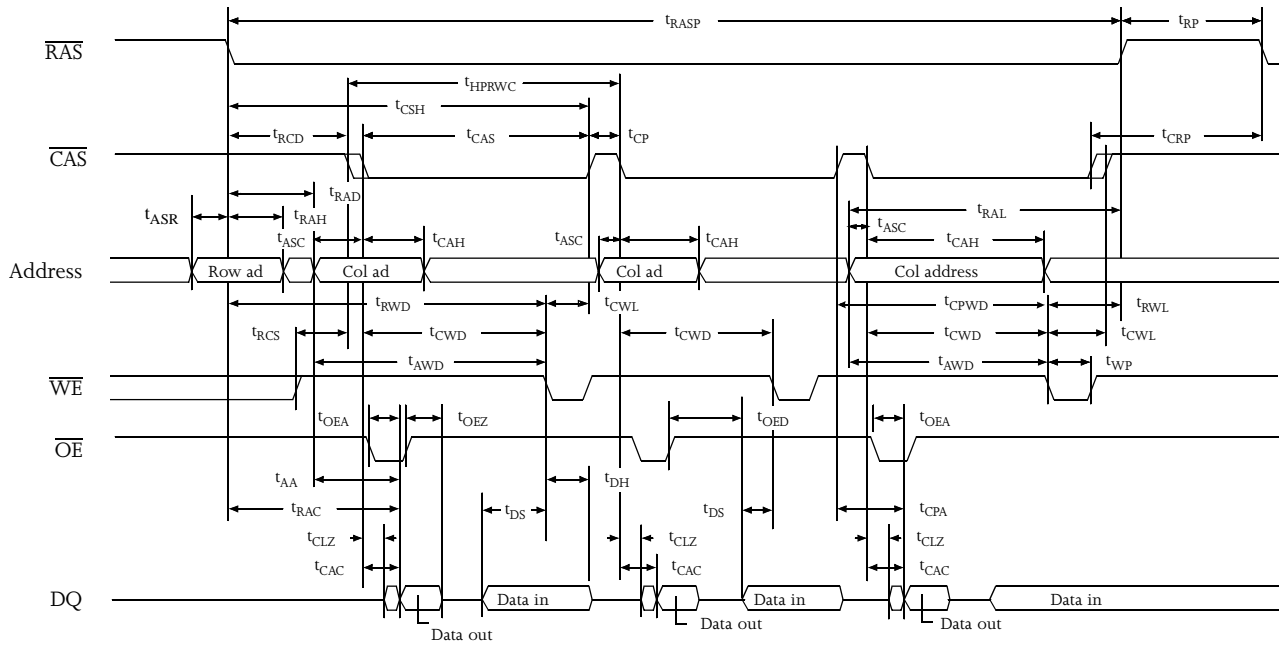


EDO page mode early write waveform



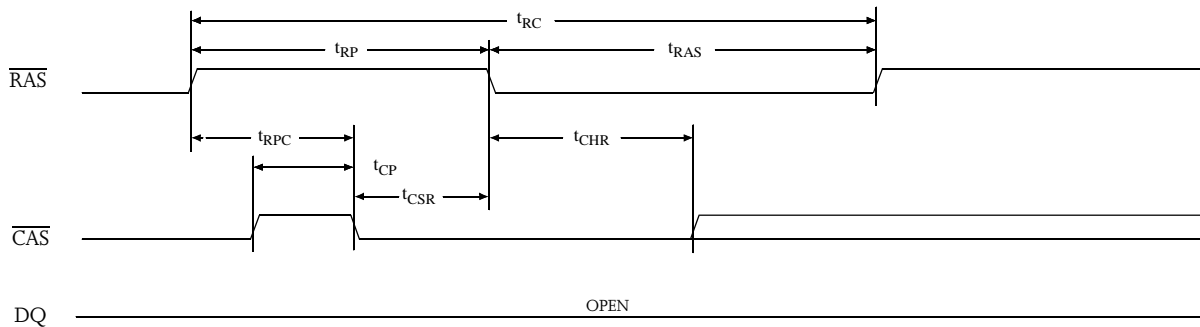


EDO page mode read-modify-write waveform



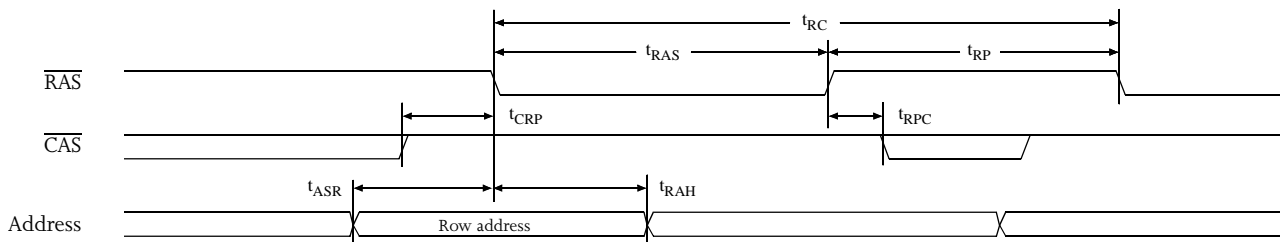
$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh waveform

$\overline{\text{WE}} = V_{\text{IH}}$



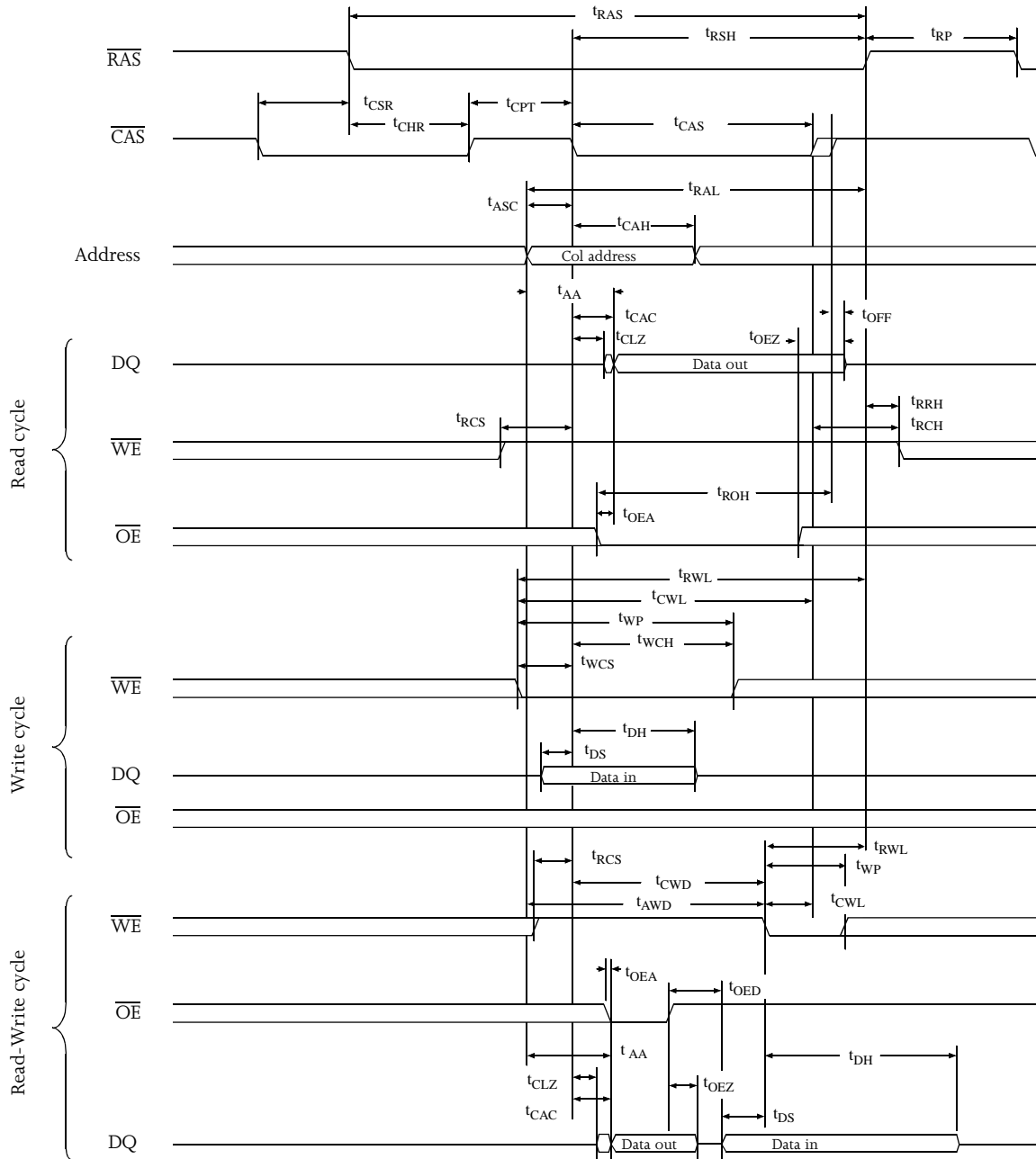
$\overline{\text{RAS}}$ only refresh waveform

$\overline{\text{WE}} = \overline{\text{OE}} = V_{\text{IH}}$ or V_{IL}



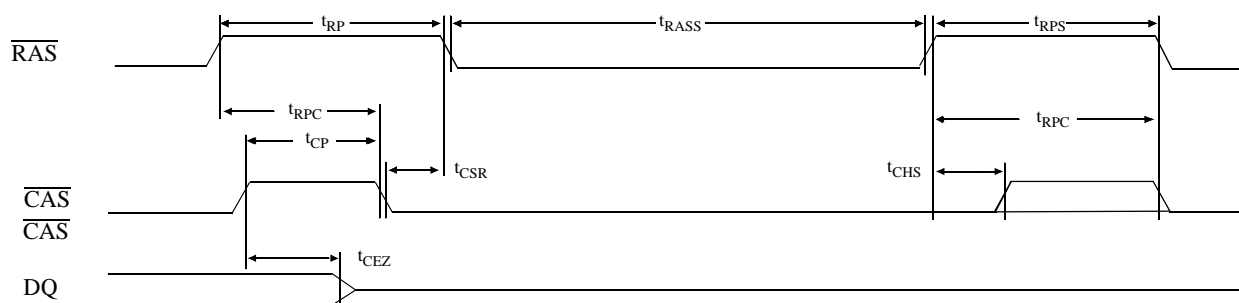


CAS before RAS refresh counter test waveform





$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ self refresh cycle



Capacitance ¹⁵

$f = 1 \text{ MHz}$, $T_a = \text{Room temperature}$

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C_{IN1}	A0 to A11	$V_{in} = 0V$	5	pF
	C_{IN2}	$\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$	$V_{in} = 0V$	7	pF
DQ capacitance	C_{DQ}	DQ0 to DQ3	$V_{in} = V_{out} = 0V$	7	pF

AS4LC4M4E0 ordering information

Package \ $\overline{\text{RAS}}$ access time	50 ns	60 ns
Plastic SOJ, 300 mil, 24/26-pin	AS4LC4M4E0-50JC AS4LC4M4E0-50JI	AS4LC4M4E0-60JC AS4LC4M4E0-60JI
Plastic TSOP, 300 mil, 24/26-pin	AS4LC4M4E0-50TC AS4LC4M4E0-50TI	AS4LC4M4E0-60TC AS4LC4M4E0-60TI

AS4LC4M4E1 ordering information

Package \ $\overline{\text{RAS}}$ access time	50 ns	60 ns
Plastic SOJ, 300 mil, 24/26-pin	AS4LC4M4E1-50JC AS4LC4M4E1-50JI	AS4LC4M4E1-60JC AS4LC4M4E1-60JI
Plastic TSOP, 300 mil, 24/26-pin	AS4LC4M4E1-50TC AS4LC4M4E1-50TI	AS4LC4M4E1-60TC AS4LC4M4E1-60TI

AS4LC4M4E0 family part numbering system

AS4	C	4M4	E0	-XX	X	X
DRAM prefix	C = 5V CMOS LC = 3V CMOS	4M×4	E0=4K refresh E1=2K refresh	$\overline{\text{RAS}}$ access time	Package: J = SOJ 300 mil, 24/26 T = TSOP 300 mil, 24/26	Temperature range C=Commercial, 0°C to 70°C I=Industrial, -40°C to 85°C

© Copyright Alliance Semiconductor Corporation. All rights reserved. Our three-point logo, our name and Intelliwatt are trademarks or registered trademarks of Alliance. All other brand and product names may be the trademarks of their respective companies. Alliance reserves the right to make changes to this document and its products at any time without notice. Alliance assumes no responsibility for any errors that may appear in this document. The data contained herein represents Alliance's best data and/or estimates at the time of issuance. Alliance reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general descriptive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warranty to any user or customer. Alliance does not assume any responsibility or liability arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of Alliance products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as expressly agreed to in Alliance's Terms and Conditions of Sale (which are available from Alliance). All sales of Alliance products are made exclusively according to Alliance's Terms and Conditions of Sale. The purchase of products from Alliance does not convey a license under any patent rights, copyrights, mask works rights, trademarks, or any other intellectual property rights of Alliance or third parties. Alliance does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of Alliance products in such life-supporting systems implies that the manufacturer assumes all risk of such use and agrees to indemnify Alliance against all claims arising from such use.